

NCE N-Channel Super Trench II Power MOSFET

Description

The NCEP035N60AG uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

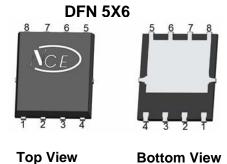
Application

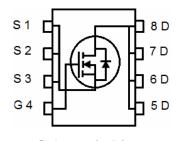
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- V_{DS} =60V,I_D =110A
 - $$\begin{split} R_{DS(ON)} = &2.8 m\Omega \text{ (typical) @ V}_{GS} = &10 \text{V} \\ R_{DS(ON)} = &3.5 m\Omega \text{ (typical) @ V}_{GS} = &4.5 \text{V} \end{split}$$
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!





Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P035N60AG	NCEP035N60AG	DFN5X6-8L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous (Silicon Limited)	I _D	110	А
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	77	Α
Pulsed Drain Current	I _{DM}	440	А
Maximum Power Dissipation	P _D	85	W
Derating factor		0.68	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	520	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 150	$^{\circ}\!\mathbb{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{ heta JC}$	1.47	°C/W

NCEP035N60AG

Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =60 V , V_{GS} =0 V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.7	2.4	V
Drain Course On State Resistance		V _{GS} =10V, I _D =55A	-	2.8	3.5	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =55A	-	3.5	4.5	mΩ
Forward Transconductance	g FS	V_{DS} =5 V , I_{D} =55 A	40	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\\ 00\\\\ 0\\	-	4000	-	PF
Output Capacitance	C _{oss}	V_{DS} =30V, V_{GS} =0V, F=1.0MHz	-	605	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIHZ	-	44	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	11	-	nS
Turn-on Rise Time	t _r	V_{DD} =30 V , I_{D} =55 A	-	5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =4.7 Ω	-	49	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg	\/ -20\/ L -55A	-	73		nC
Gate-Source Charge	Q _{gs}	V_{DS} =30V, I_{D} =55A, V_{GS} =10V	-	12.5		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	11		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =55A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	110	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C$, $I_F = I_S$	-	48		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	60		nC

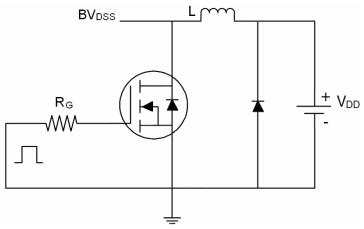
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V_DD=30V,V_G=10V,L=0.5mH,Rg=25 Ω

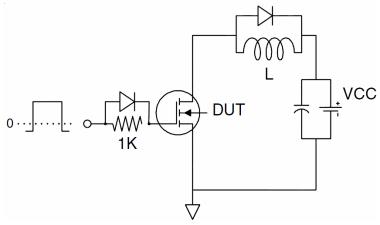


Test Circuit

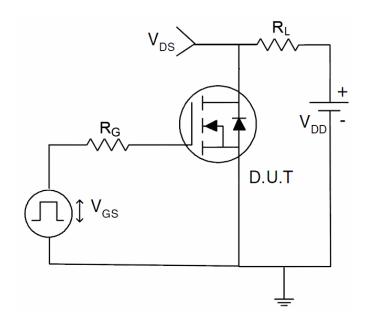
1) E_{AS} test Circuit



2) Gate charge test Circuit

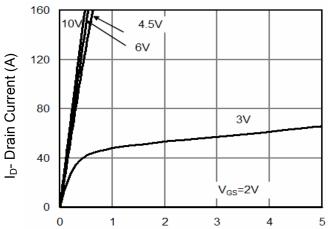


3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)



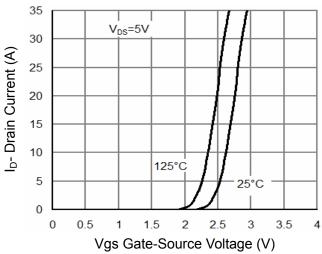


Figure 2 Transfer Characteristics

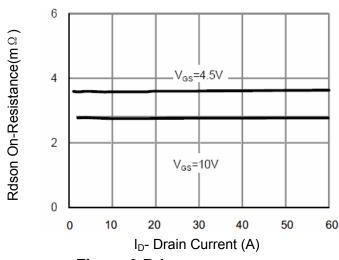
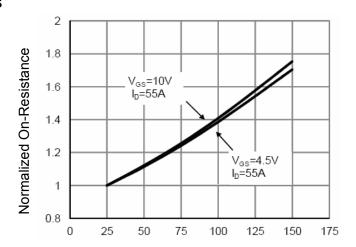


Figure 3 Rdson- Drain Current



T_J-Junction Temperature(°C)

Figure 4 Rdson-JunctionTemperature

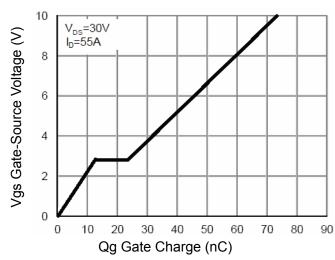


Figure 5 Gate Charge

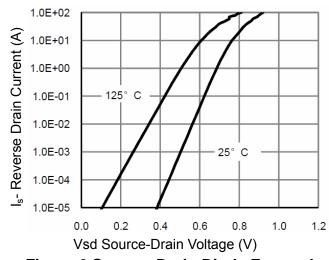


Figure 6 Source- Drain Diode Forward



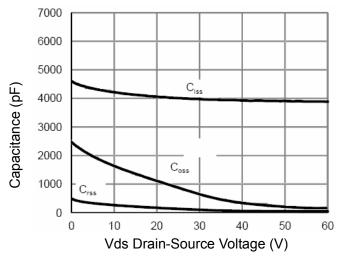


Figure 7 Capacitance vs Vds

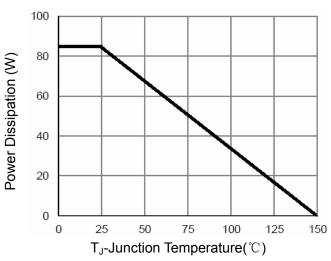


Figure 9 Power De-rating

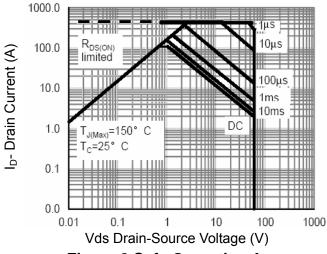


Figure 8 Safe Operation Area

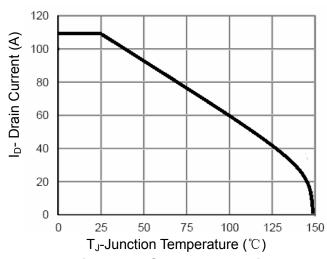


Figure 10 Current De-rating

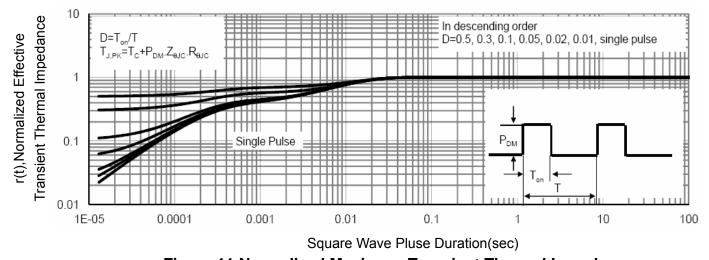
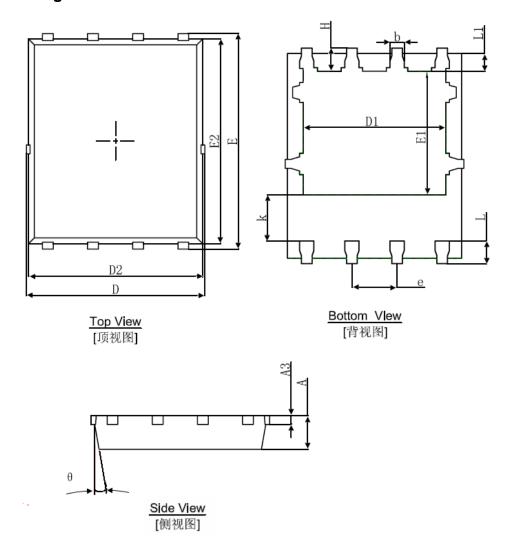


Figure 11 Normalized Maximum Transient Thermal Impedance



DFN5X6-8L Package Information



Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	0.900	1.000	0.035	0.039	
A3	0.254	0.254REF.		REF.	
D	4.944	5.096	0.195	0.201	
E	5.974	6.126	0.235	0.241	
D1	3.910	4.110	0.154	0.162	
E1	3.375	3.575	0.133	0.141	
D2	4.824	4.976	0.190	0.196	
E2	5.674	5.826	0.223	0.229	
k	1.190	1.390	0.047	0.055	
b	0.350	0.450	0.014	0.018	
е	1.270	TYP.	0.050TYP.		
L	0.559	0.711	0.022	0.028	
L1	0.424	0.576	0.017	0.023	
Н	0.574	0.726	0.023	0.029	
θ	8°	12°	8°	12°	

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NCEP035N60AG

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